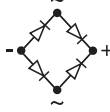
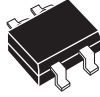




CBRHDSH2-100

**SURFACE MOUNT SILICON
HIGH DENSITY
2.0 AMP DUAL IN LINE
SCHOTTKY BRIDGE RECTIFIER**

HD BRIDGE



HD DIP CASE

* Device is **Halogen Free** by design

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRHDSH2-100 is a full wave bridge rectifier mounted in a durable epoxy surface mount case, utilizing glass passivated chips.

MARKING CODE: CSH10

FEATURES:

- Low Leakage Current (700nA TYP @ V_{RRM})
- High 2.0A Current Rating
- Low V_F Schottky Diodes (840mV MAX @ $I_F=2.0A$)

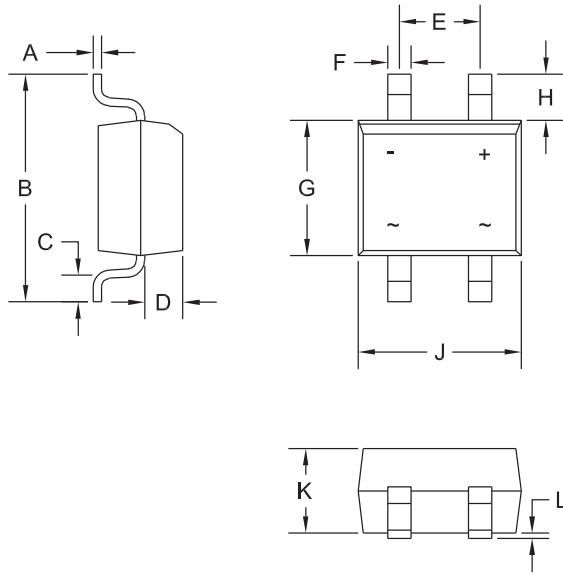
MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
DC Blocking Voltage	V_R	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	V
Average Forward Current, $T_A=75^\circ\text{C}$	I_O	2.0	A
Peak Forward Surge Current (8.3ms)	I_{FSM}	50	A
Operating Junction Temperature Range	T_J	-50 to +125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-50 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
I_R	$V_R=100V$	0.70	4.0	μA
V_F	$I_F=500\text{mA}$	610		mV
V_F	$I_F=1.0A$	700		mV
V_F	$I_F=2.0A$	770	840	mV
C_J	$V_R=4.0V, f=1.0\text{MHz}$		250	pF

HD DIP CASE - MECHANICAL OUTLINE



R2

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.006	0.014	0.15	0.35
B	-	0.275	-	7.00
C	0.027	0.043	0.70	1.10
D	0.035	0.051	0.90	1.30
E	0.090	0.106	2.30	2.70
F	0.019	0.031	0.50	0.80
G	0.150	0.165	3.80	4.20
H	0.051	0.067	1.30	1.70
J	0.177	0.193	4.50	4.90
K	0.090	0.106	2.30	2.70
L	0.000	0.008	0.00	0.20

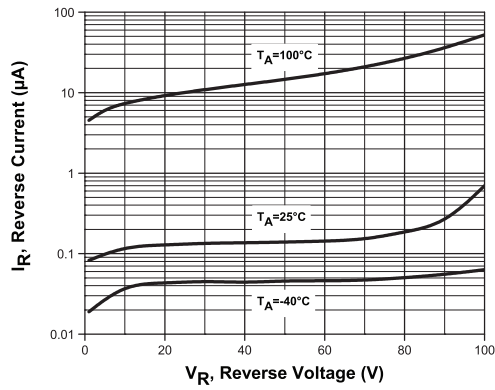
HD DIP (REV: R2)

MARKING CODE: CSH10

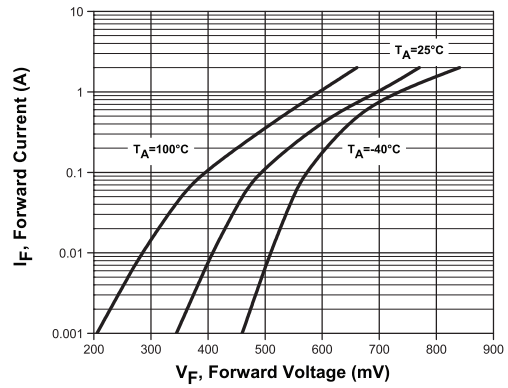
R2 (8-October 2009)

TYPICAL ELECTRICAL CHARACTERISTICS

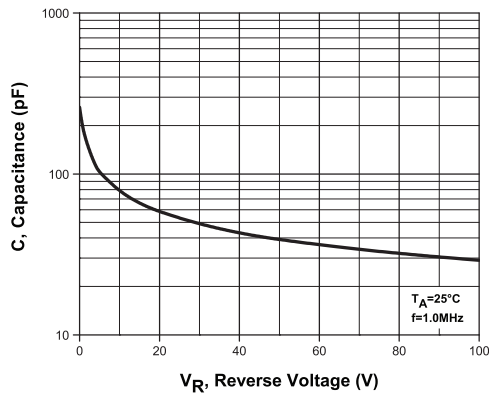
Typical Per Diode Leakage Current



Typical Per Diode Forward Voltage



Typical Per Diode Capacitance



Per Diode Current Derating

